

**Amendments to the Specification:**

Please amend the above-identified application as follows:

Applicant accepts the proposed corrections to the specification required by the Examiner and hereby revises the specification accordingly, without adding new matter:

***Page 3 [sic, 4], line 17 (entire paragraph included herein):***

Accordingly, a high pressure chemical vapor trapping system to separate and collect elements of a chemical vapor exhaust is provided. The system comprises a hot trap and a cold trap connected to each other as a single unit. The exhaust pump is upstream of the hot and cold trapping system, providing high pressure in the hot trap. While prior art positions the hot trap upstream of the exhaust pump to avoid damage to the pump, we found no significant damage to the exhaust pump by having the pump connected directly to the process chamber. The reason is that the pump temperature is much lower than most process temperatures, and most processes require high temperature for deposition; thus, there is minimum deposition at the pump. With use of a wet pump, the only side effect is the faster degradation of the pump oil, thus needing a more frequent oil changing schedule. However, [[the]] the use of a dry pump, which uses no oil, positioning the pump upstream of the hot and cold trapping system has no effect on the pump. Since a dry pump typically runs at less than ~ 70°C, and a wet pump runs at room temperature, and since deposition processes run at much higher temperatures, e.g., typically 200°C for MOCVD copper deposition; 400-500°C for PECVD deposition; and 1000-1100°C for rapid thermal deposition, the prior art concern about significant deposition at the pump, leading to degradation of the pump, is not a concern using this invention.